

# 2SC3052-T150

FOR LOW FREQUENCY AMPLIFY APPLICATION  
SILICON NPN EPITAXIAL TYPE

AEC-Q101 Compliance

## DESCRIPTION

2SC3052 is a mini package resin sealed silicon NPN epitaxial transistor, It is designed for low frequency voltage application.

## FEATURE

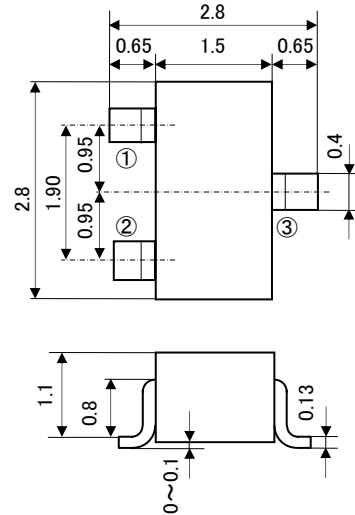
- Small collector to emitter saturation voltage.  
VCE(sat)=0.3V max (@IC=100mA/IB=10mA)
- Excellent linearity of DC forward current gain.
- Super mini package for easy mounting

## APPLICATION

For Hybrid IC, Small type machine low frequency voltage amplify application.

## OUTLINE DRAWING

Unit: mm



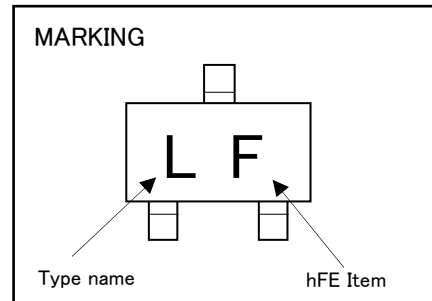
## TERMINAL CONNECTER

- ①: BASE JEITA: SC-59
- ②: EMITTER JEDEC: Similar to TO-236
- ③: COLLECTOR

## MAXIMUM RATINGS (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to Base voltage	V <sub>CBO</sub>	50	V
Emitter to Base voltage	V <sub>EBO</sub>	6	V
Collector to Emitter voltage	V <sub>CEO</sub>	50	V
Collector current	I <sub>O</sub>	200	mA
Collector dissipation	P <sub>c</sub>	200	mW
Junction temperature	T <sub>j</sub>	+150	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

## MARKING



## ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Test conditions	Limits			Unit
			Min	Typ	Max	
C to E breakdown voltage	V(BR) <sub>CEO</sub>	I <sub>C</sub> =100μA, R <sub>BE</sub> =∞	50	-	-	V
Collector cut off current	ICBO	V <sub>CB</sub> =50V, I <sub>E</sub> =0mA	-	-	0.1	μA
Emitter cut off current	IEBO	V <sub>EB</sub> =6V, I <sub>C</sub> =0mA	-	-	0.1	μA
DC forward current gain ※	hFE	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	150	-	500	-
DC forward current gain	hFE	V <sub>CE</sub> =6V, I <sub>C</sub> =0.1mA	90	-	-	-
C to E Saturation voltage	VCE(sat)	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA	-	-	0.3	V
B to E Saturation voltage	VBE(sat)	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA	-	-	1.0	V
Gain bandwidth product	fT	V <sub>CE</sub> =6V, I <sub>E</sub> =-10mA	-	200	-	MHz
Collector output capacitance	Cob	V <sub>CB</sub> =6V, I <sub>E</sub> =0, f=1MHz	-	2.5	-	pF
Noise figure	NF	V <sub>CE</sub> =6V, I <sub>E</sub> =-0.1mA, f=1kHz, RG=2kΩ	-	-	15	dB

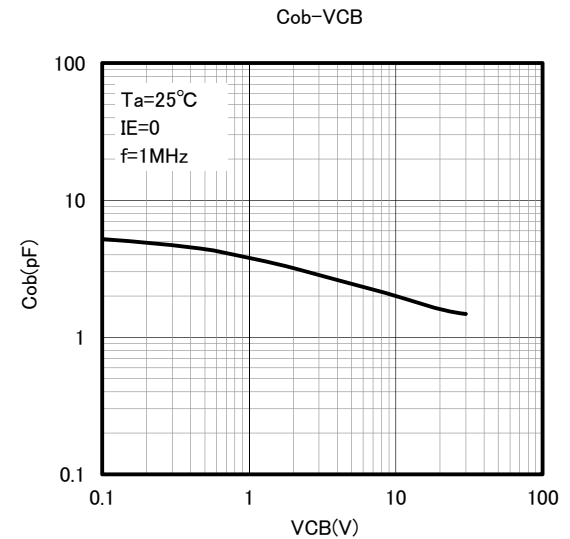
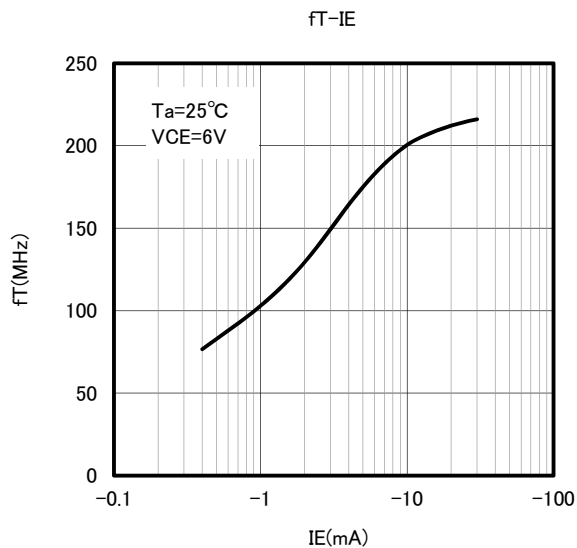
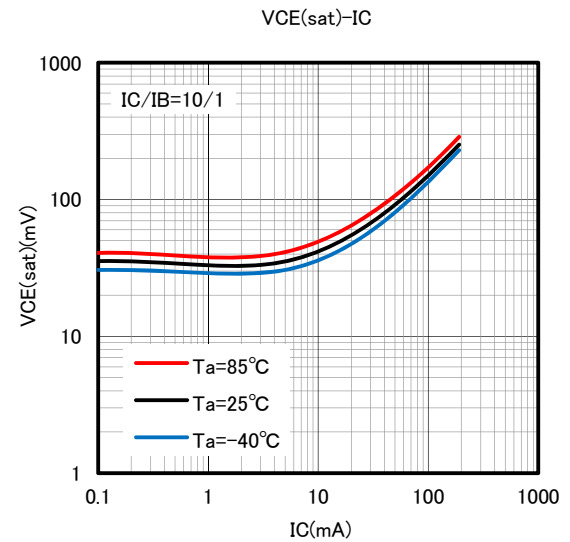
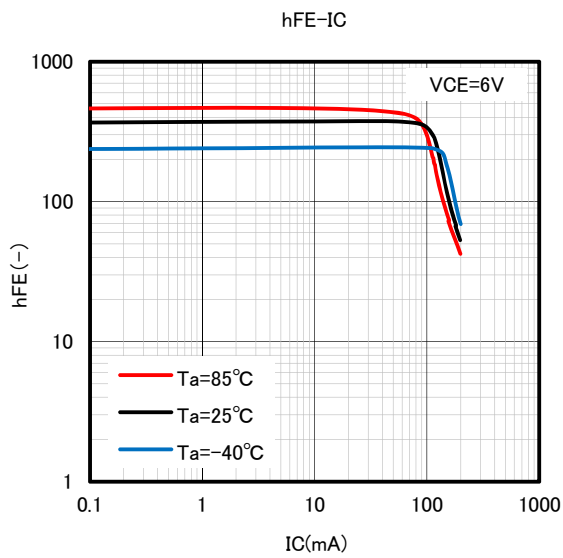
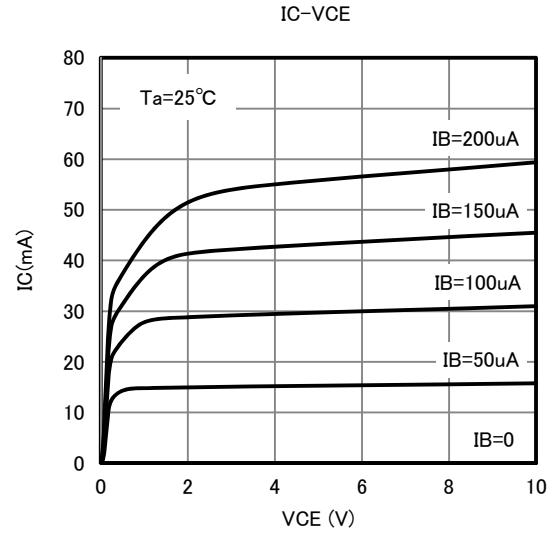
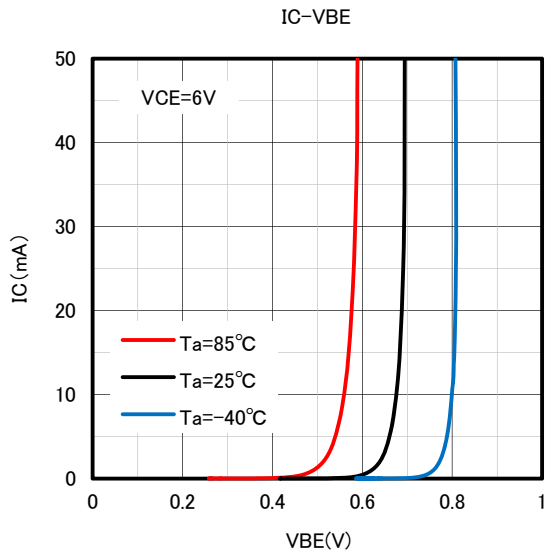
※) It shows hFE classification at right table.

Item	E	F
hFE Item	150~300	250~500

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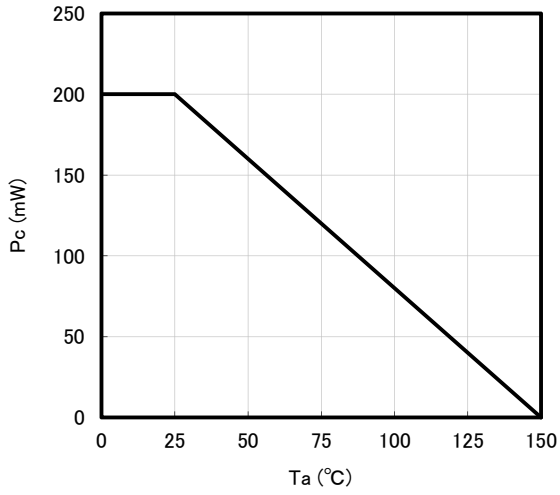
## TYPICAL CHARACTERISTICS



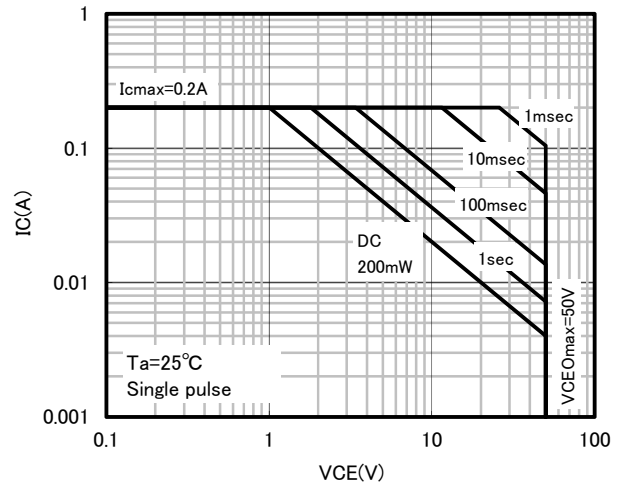
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FOR LOW FREQUENCY AMPLIFY APPLICATION  
SILICON NPN EPITAXIAL TYPE

Pc-Ta



ASO





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